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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, Motor Control PWM, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	37
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	10K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f103c6t6

2.3.13 DMA

The flexible 7-channel general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with support for software trigger on each channel. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I²C, USART, general-purpose and advanced-control timers TIMx and ADC.

2.3.14 RTC (real-time clock) and backup registers

The RTC and the backup registers are supplied through a switch that takes power either on V_{DD} supply when present or through the V_{BAT} pin. The backup registers are ten 16-bit registers used to store 20 bytes of user application data when V_{DD} power is not present.

The real-time clock provides a set of continuously running counters which can be used with suitable software to provide a clock calendar function, and provides an alarm interrupt and a periodic interrupt. It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-power RC has a typical frequency of 40 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural crystal deviation. The RTC features a 32-bit programmable counter for long-term measurement using the Compare register to generate an alarm. A 20-bit prescaler is used for the time base clock and is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

2.3.15 Timers and watchdogs

The low-density STM32F103xx performance line devices include an advanced-control timer, two general-purpose timers, two watchdog timers and a SysTick timer.

[Table 4](#) compares the features of the advanced-control and general-purpose timers.

Table 4. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM1	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	Yes
TIM2, TIM3	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No

2.3.21 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current-capable.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

I/Os on APB2 with up to 18 MHz toggling speed.

2.3.22 ADC (analog-to-digital converter)

Two 12-bit analog-to-digital converters are embedded into STM32F103xx performance line devices and each ADC shares up to 16 external channels, performing conversions in single-shot or scan modes. In scan mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold
- Single shunt

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) and the advanced-control timer (TIM1) can be internally connected to the ADC start trigger, injection trigger, and DMA trigger respectively, to allow the application to synchronize A/D conversion and timers.

2.3.23 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between $2\text{ V} < V_{\text{DDA}} < 3.6\text{ V}$. The temperature sensor is internally connected to the ADC12_IN16 input channel which is used to convert the sensor output voltage into a digital value.

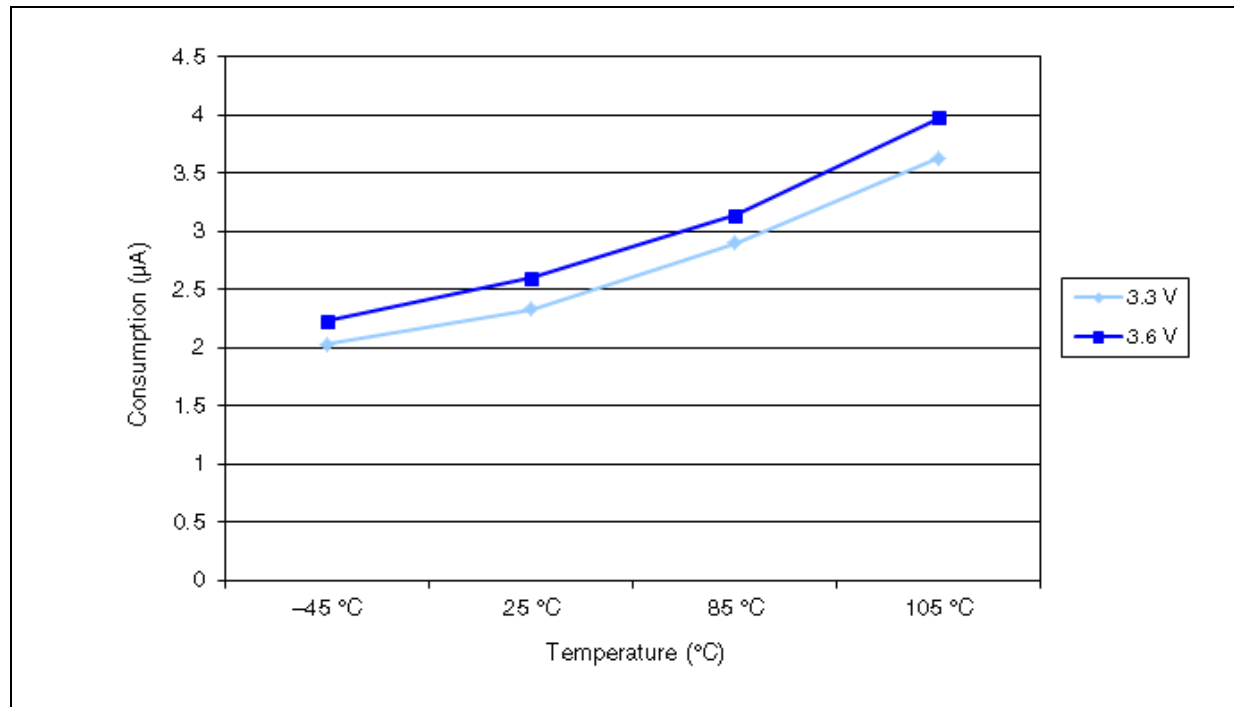
2.3.24 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

Table 5. Low-density STM32F103xx pin definitions

Pins				Pin name	Type ⁽¹⁾	I/O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Alternate functions ⁽⁴⁾	
LQFP48/ UFQFPN48	LQFP64	TFBGA64	VFQFPN36					Default	Remap
1	1	B2	-	V _{BAT}	S	-	V _{BAT}	-	-
2	2	A2	-	PC13-TAMPER-RTC ⁽⁵⁾	I/O	-	PC13 ⁽⁶⁾	TAMPER-RTC	-
3	3	A1	-	PC14-OSC32_IN ⁽⁵⁾	I/O	-	PC14 ⁽⁶⁾	OSC32_IN	-
4	4	B1	-	PC15-OSC32_OUT ⁽⁵⁾	I/O	-	PC15 ⁽⁶⁾	OSC32_OUT	-
5	5	C1	2	OSC_IN	I	-	OSC_IN	-	PD0 ⁽⁷⁾
6	6	D1	3	OSC_OUT	O	-	OSC_OUT	-	PD1 ⁽⁷⁾
7	7	E1	4	NRST	I/O	-	NRST	-	-
-	8	E3	-	PC0	I/O	-	PC0	ADC12_IN10	-
-	9	E2	-	PC1	I/O	-	PC1	ADC12_IN11	-
-	10	F2	-	PC2	I/O	-	PC2	ADC12_IN12	-
-	11	-	-	PC3	I/O	-	PC3	ADC12_IN13	-
-	-	G1	-	V _{REF+} ⁽⁸⁾	S	-	V _{REF+}	-	-
8	12	F1	5	V _{SSA}	S	-	V _{SSA}	-	-
9	13	H1	6	V _{DDA}	S	-	V _{DDA}	-	-
10	14	G2	7	PA0-WKUP	I/O	-	PA0	WKUP/USART2_CTS/ ADC12_IN0/ TIM2_CH1_ETR ⁽⁹⁾	-
11	15	H2	8	PA1	I/O	-	PA1	USART2_RTS/ ADC12_IN1/TIM2_CH2 ⁽⁹⁾	-
12	16	F3	9	PA2	I/O	-	PA2	USART2_TX/ ADC12_IN2/TIM2_CH3 ⁽⁹⁾	-
13	17	G3	10	PA3	I/O	-	PA3	USART2_RX/ ADC12_IN3/TIM2_CH4 ⁽⁹⁾	-
-	18	C2	-	V _{SS_4}	S	-	V _{SS_4}	-	-
-	19	D2	-	V _{DD_4}	S	-	V _{DD_4}	-	-
14	20	H3	11	PA4	I/O	-	PA4	SPI1_NSS ⁽⁹⁾ / USART2_CK/ADC12_IN4	-
15	21	F4	12	PA5	I/O	-	PA5	SPI1_SCK ⁽⁹⁾ /ADC12_IN5	-
16	22	G4	13	PA6	I/O	-	PA6	SPI1_MISO ⁽⁹⁾ / ADC12_IN6/TIM3_CH1 ⁽⁹⁾	TIM1_BKIN
17	23	H4	14	PA7	I/O	-	PA7	SPI1_MOSI ⁽⁹⁾ / ADC12_IN7/TIM3_CH2 ⁽⁹⁾	TIM1_CH1N
-	24	H5	-	PC4	I/O	-	PC4	ADC12_IN14	-
-	25	H6	-	PC5	I/O	-	PC5	ADC12_IN15	-

Figure 18. Typical current consumption in Standby mode versus temperature at $V_{DD} = 3.3\text{ V}$ and 3.6 V



Typical current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load).
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash access time is adjusted to f_{HCLK} frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states above).
- Ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).
- Prefetch is ON (Reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK}/4$, $f_{PCLK2} = f_{HCLK}/2$, $f_{ADCCLK} = f_{PCLK2}/4$

Figure 19. High-speed external clock source AC timing diagram

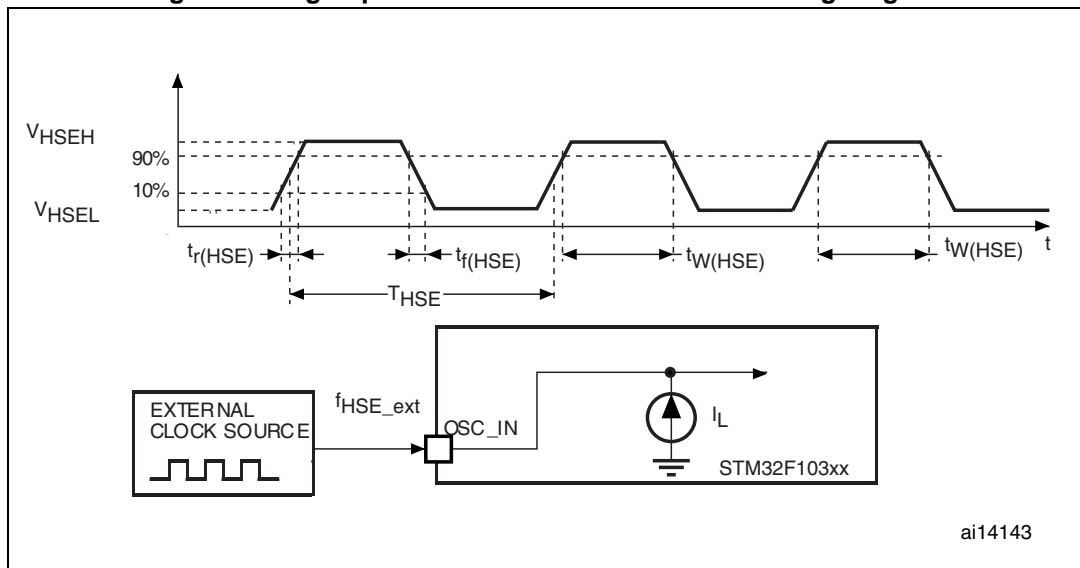
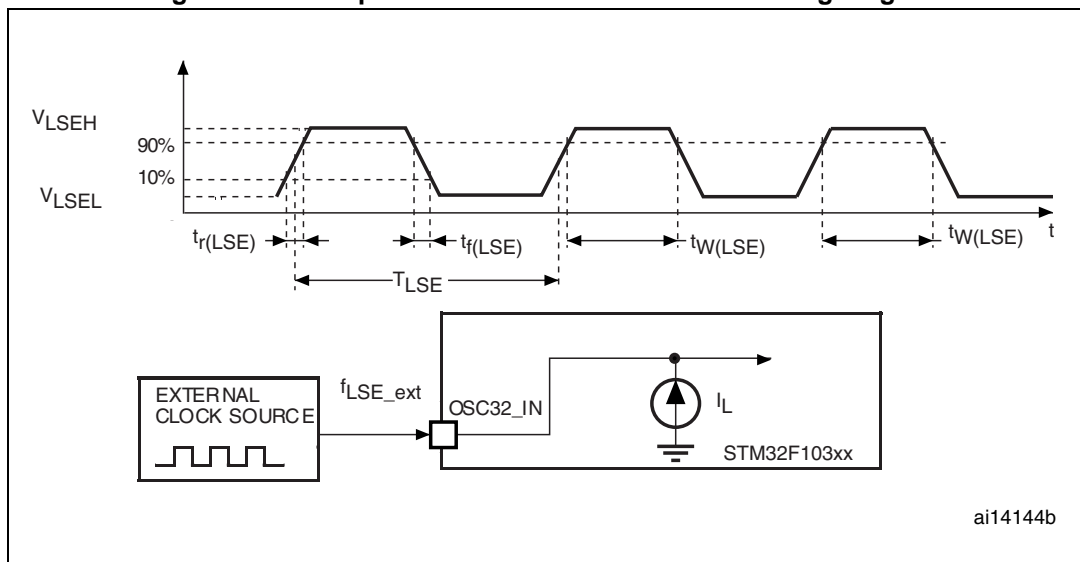


Figure 20. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 16 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 22](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

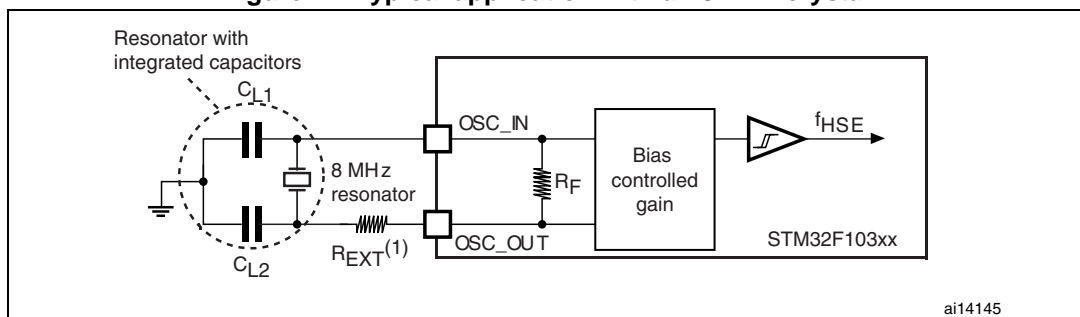
Table 22. HSE 4-16 MHz oscillator characteristics^{(1) (2)}

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	16	MHz
R_F	Feedback resistor	-	-	200	-	k Ω
C	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S) ⁽³⁾	$R_S = 30 \Omega$	-	30	-	pF
i_2	HSE driving current	$V_{DD} = 3.3 V$, $V_{IN} = V_{SS}$ with 30 pF load	-	-	1	mA
g_m	Oscillator transconductance	Startup	25	-	-	mA/V
$t_{SU(HSE)}$ ⁽⁴⁾	startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Based on characterization, not tested in production.
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 21](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 21. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 23](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization

Table 28. Flash memory characteristics (continued)

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
I _{DD}	Supply current	Read mode f _{HCLK} = 72 MHz with 2 wait states, V _{DD} = 3.3 V	-	-	20	mA
		Write / Erase modes f _{HCLK} = 72 MHz, V _{DD} = 3.3 V	-	-	5	mA
		Power-down mode / Halt, V _{DD} = 3.0 to 3.6 V	-	-	50	μA
V _{prog}	Programming voltage	-	2	-	3.6	V

1. Guaranteed by design, not tested in production.

Table 29. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value			Unit
			Min ⁽¹⁾	Typ	Max	
N _{END}	Endurance	T _A = -40 to +85 °C (6 suffix versions) T _A = -40 to +105 °C (7 suffix versions)	10	-	-	kcycles
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 85 °C	30	-	-	Years
		1 kcycle ⁽²⁾ at T _A = 105 °C	10	-	-	
		10 kcycles ⁽²⁾ at T _A = 55 °C	20	-	-	

1. Based on characterization, not tested in production.

2. Cycling performed over the whole temperature range.

5.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB:** A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 30](#). They are based on the EMS levels and classes defined in application note AN1709.

5.3.11 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts \times (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 32. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
$V_{\text{ESD(HBM)}}$	Electrostatic discharge voltage (human body model)	$T_A = +25\text{ }^{\circ}\text{C}$ conforming to JESD22-A114	2	2000	V
$V_{\text{ESD(CDM)}}$	Electrostatic discharge voltage (charge device model)	$T_A = +25\text{ }^{\circ}\text{C}$ conforming to JESD22-C101	II	500	

1. Based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 33. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

5.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

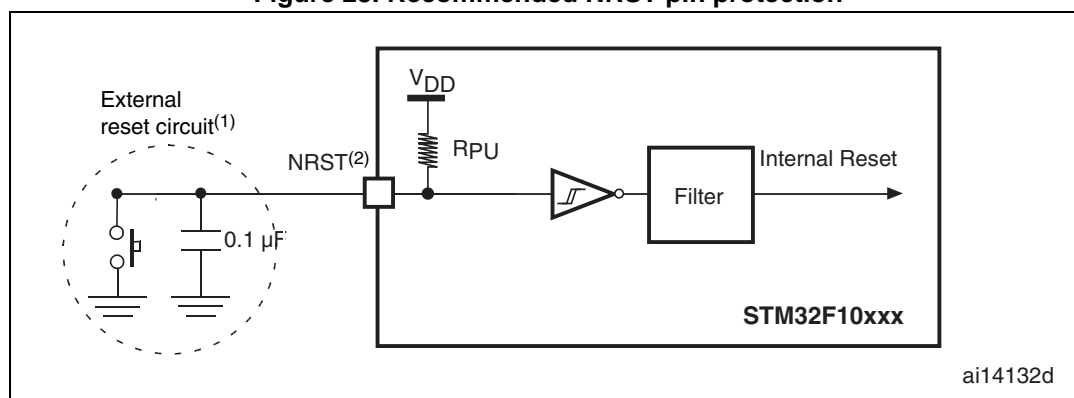
The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation).

The test results are given in [Table 34](#)

Table 34. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on OSC_IN32, OSC_OUT32, PA4, PA5, PC13	-0	+0	mA
	Injected current on all FT pins	-5	+0	
	Injected current on any other pin	-5	+5	

Figure 28. Recommended NRST pin protection



2. The reset network protects the device against parasitic resets.
3. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 38](#). Otherwise the reset will not be taken into account by the device.

5.3.15 TIM timer characteristics

The parameters given in [Table 39](#) are guaranteed by design.

Refer to [Section 5.3.12: I/O current injection characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 39. TIMx⁽¹⁾ characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 72 \text{ MHz}$	13.9	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK} = 72 \text{ MHz}$	0	36	MHz
Res_{TIM}	Timer resolution	-	-	16	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 72 \text{ MHz}$	0.0139	910	μs
t_{MAX_COUNT}	Maximum possible count	-	-	65536×65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 72 \text{ MHz}$	-	59.6	s

1. TIMx is used as a general term to refer to the TIM1, TIM2, TIM3 and TIM4 timers.

SPI interface characteristics

Unless otherwise specified, the parameters given in [Table 42](#) are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 9](#).

Refer to [Section 5.3.12: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 42. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	18	MHz
		Slave mode	-	18	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: $C = 30\text{ pF}$		8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}^{(1)}$	NSS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(NSS)}^{(1)}$	NSS hold time	Slave mode	$2t_{PCLK}$	-	
$t_{w(SCKH)}^{(1)}$ $t_{w(SCKL)}^{(1)}$	SCK high and low time	Master mode, $f_{PCLK} = 36\text{ MHz}$, presc = 4	50	60	
$t_{su(MI)}^{(1)}$ $t_{su(SI)}^{(1)}$	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}^{(1)}$ $t_{h(SI)}^{(1)}$	Data input hold time	Master mode	5	-	
		Slave mode	4	-	
$t_{a(SO)}^{(1)(2)}$	Data output access time	Slave mode, $f_{PCLK} = 20\text{ MHz}$	0	$3t_{PCLK}$	
$t_{dis(SO)}^{(1)(3)}$	Data output disable time	Slave mode	2	10	
$t_{v(SO)}^{(1)}$	Data output valid time	Slave mode (after enable edge)	-	25	
$t_{v(MO)}^{(1)}$	Data output valid time	Master mode (after enable edge)	-	5	
$t_{h(SO)}^{(1)}$ $t_{h(MO)}^{(1)}$	Data output hold time	Slave mode (after enable edge)	15	-	
		Master mode (after enable edge)	2	-	

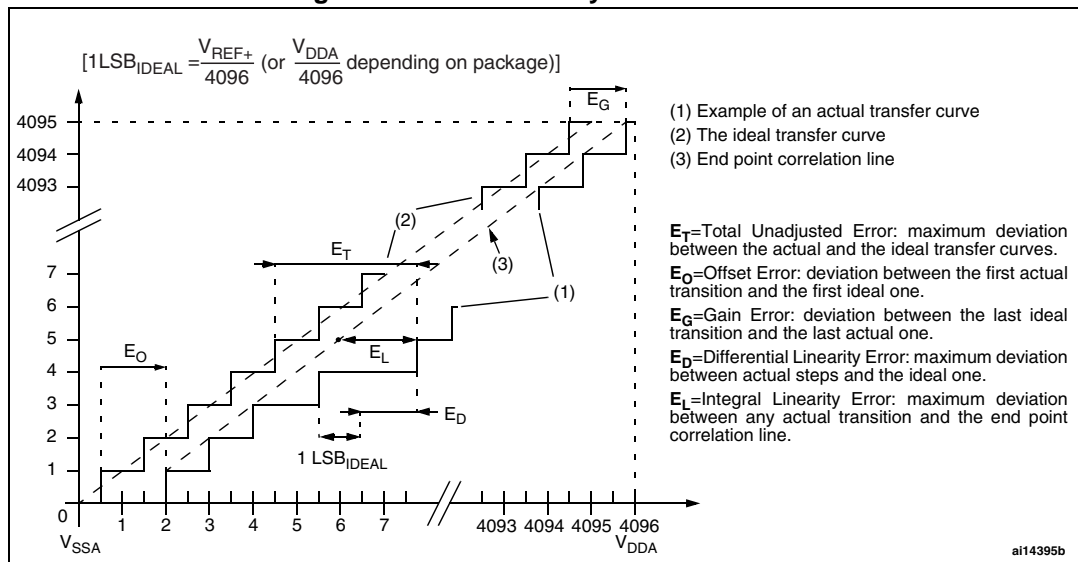
1. Based on characterization, not tested in production.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Table 49. ADC accuracy^{(1) (2) (3)}

Symbol	Parameter	Test conditions	Typ	Max ⁽⁴⁾	Unit
ET	Total unadjusted error	$f_{PCLK2} = 56 \text{ MHz}$, $f_{ADC} = 14 \text{ MHz}$, $R_{AIN} < 10 \text{ k}\Omega$, $V_{DDA} = 2.4 \text{ V to } 3.6 \text{ V}$ Measurements made after ADC calibration	± 2	± 5	LSB
EO	Offset error		± 1.5	± 2.5	
EG	Gain error		± 1.5	± 3	
ED	Differential linearity error		± 1	± 2	
EL	Integral linearity error		± 1.5	± 3	

1. ADC DC accuracy values are measured after internal calibration.
2. Better performance could be achieved in restricted V_{DD} , frequency and temperature ranges.
3. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 5.3.12](#) does not affect the ADC accuracy.
4. Based on characterization, not tested in production.

Figure 34. ADC accuracy characteristics

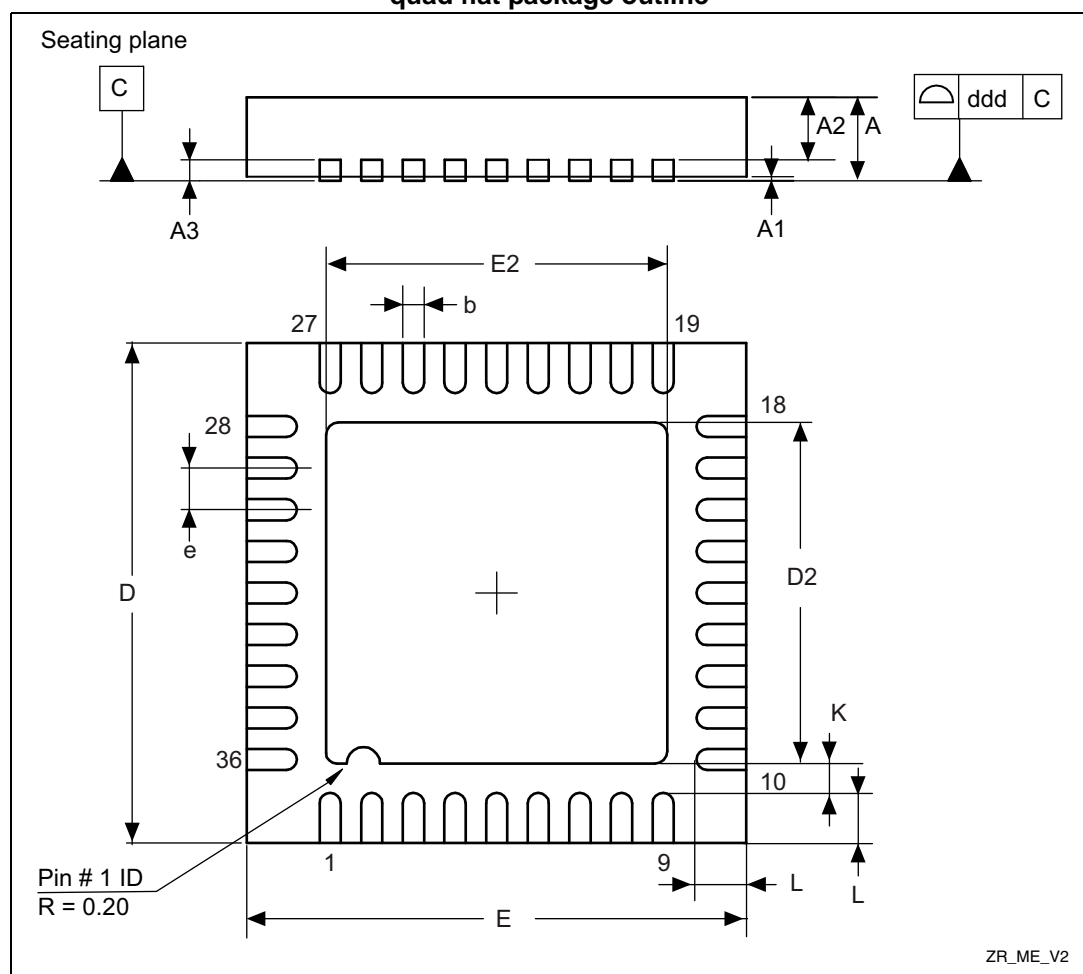


6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

6.1 VFQFPN36 Package

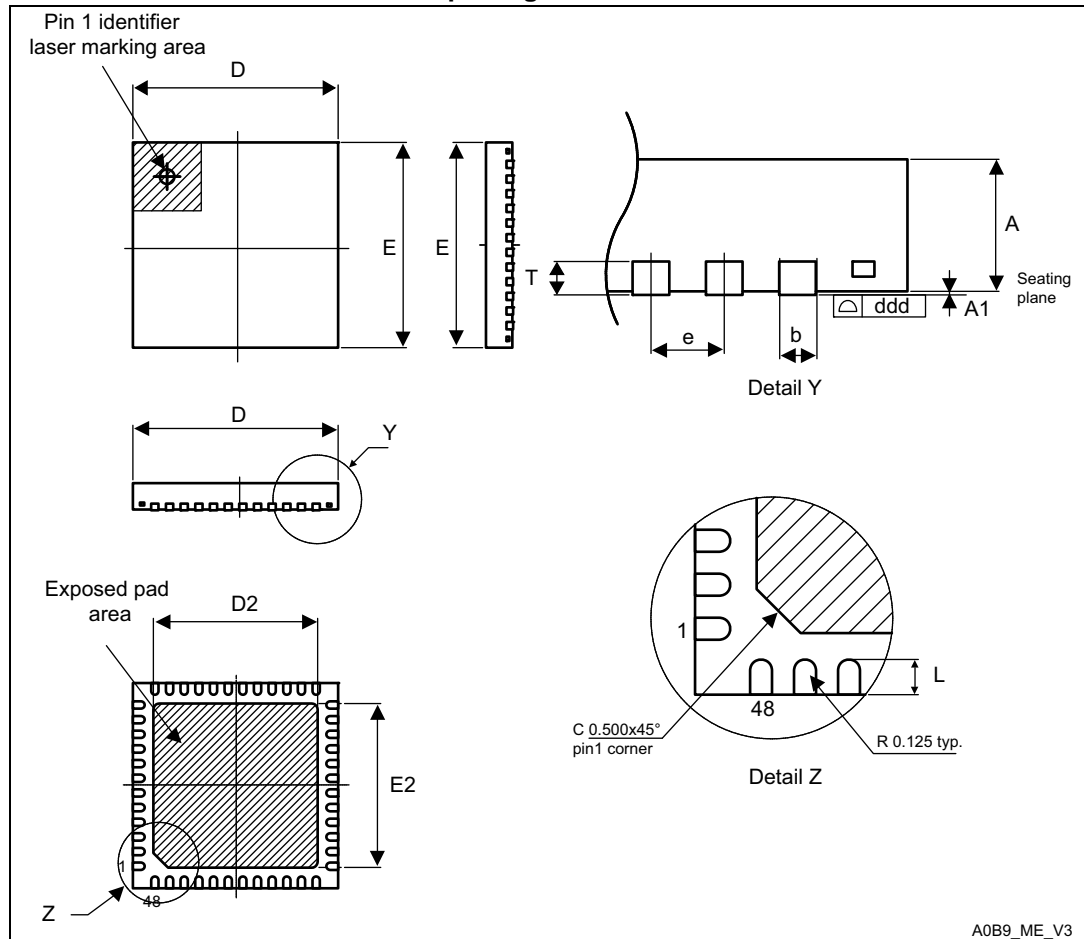
Figure 38. VFQFPN36 - 36-pin, 6x6 mm, 0.5 mm pitch very thin profile fine pitch quad flat package outline



1. Drawing is not to scale.

6.2 UFQFPN48 package information

Figure 41. UFQFPN48 - 48-lead, 7x7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package outline



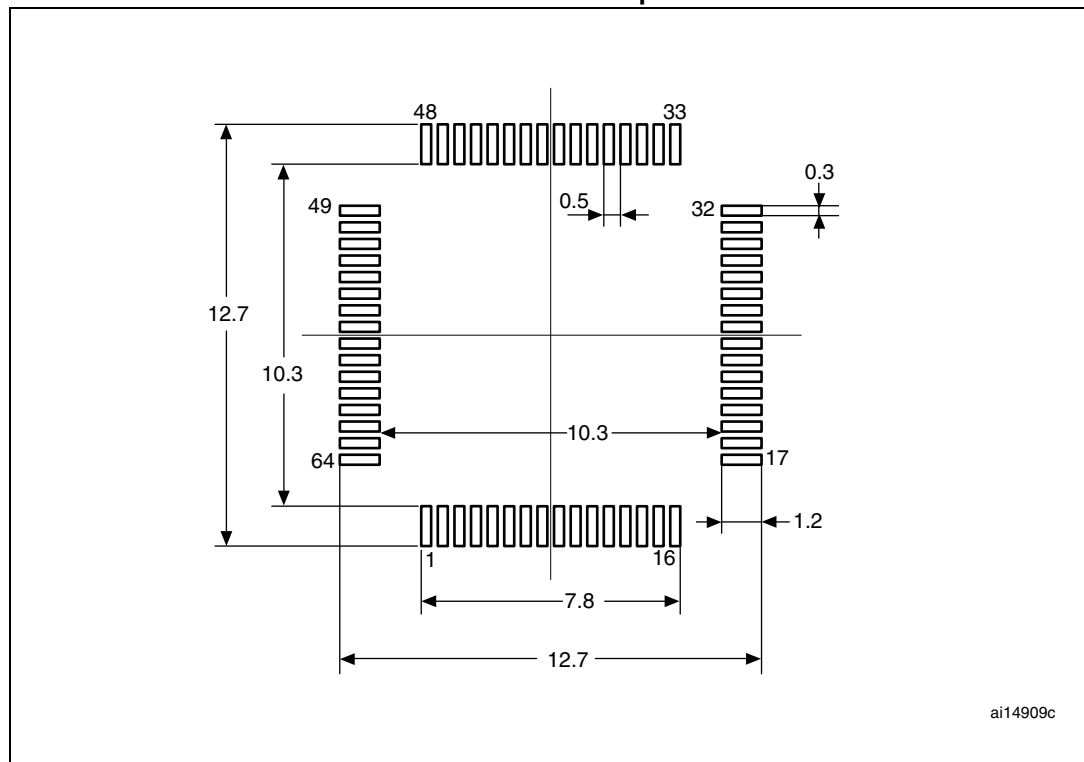
1. Drawing is not to scale.
2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

Table 53. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

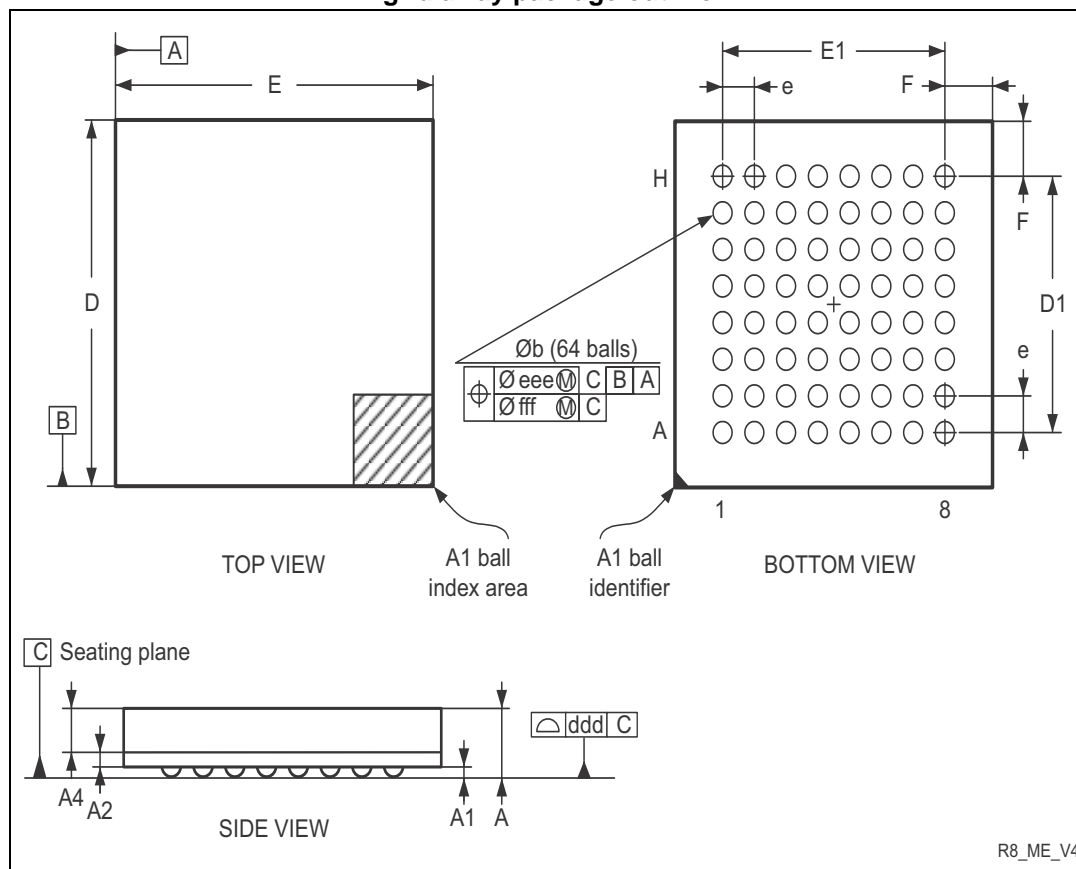
Figure 45. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

6.4 TFBGA64 package information

Figure 47. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline



1. Drawing is not to scale.

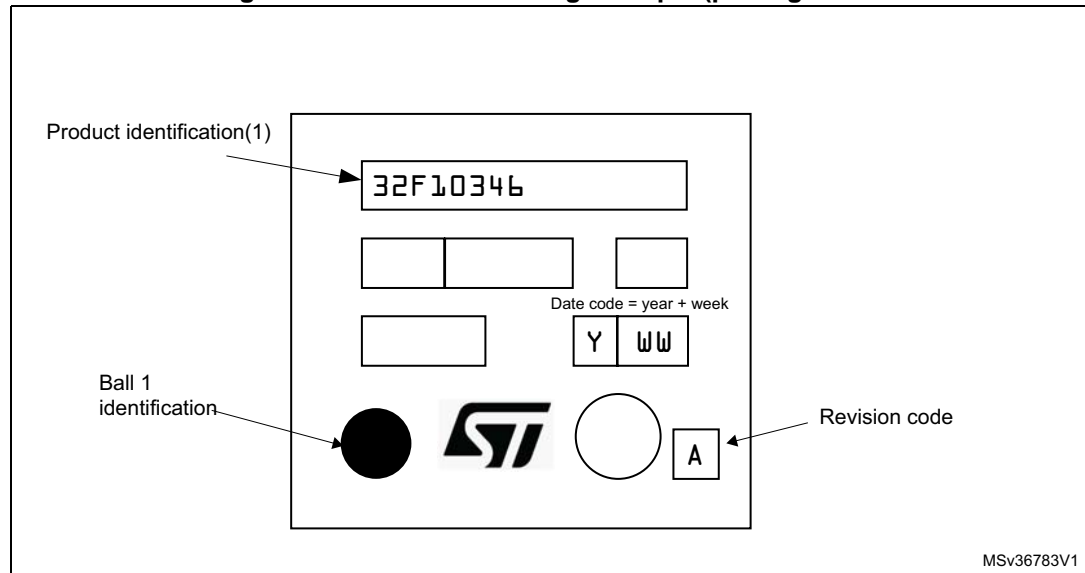
Table 54. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.200	-	-	0.0472
A1	0.150	-	-	0.0059	-	-
A2	-	0.200	-	-	0.0079	-
A4	-	-	0.600	-	-	0.0236
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	-	3.500	-	-	0.1378	-
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	-	3.500	-	-	0.1378	-

Device Marking for TFBGA64

The following figure gives an example of topside marking orientation versus ball 1 identifier location.

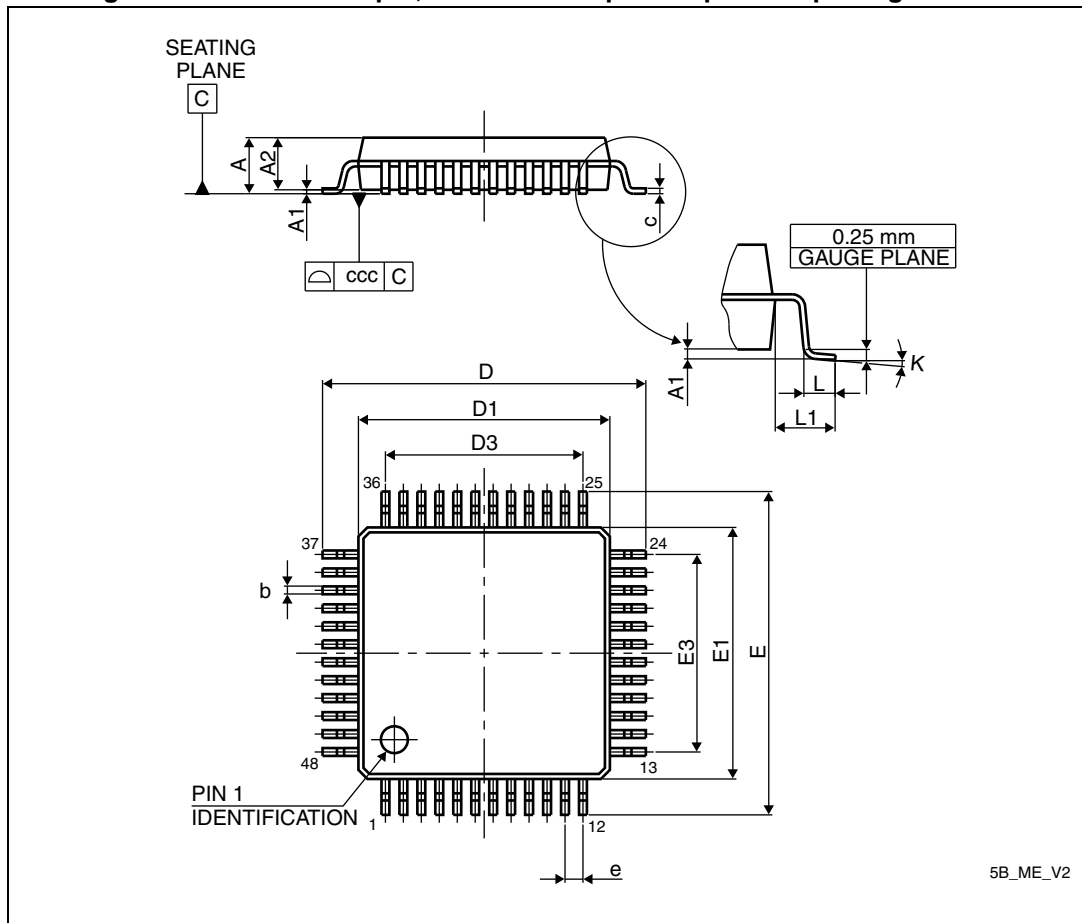
Figure 49. TFBGA64 marking example (package view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

6.5 LQFP48 package information

Figure 50. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

**Table 56. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package
mechanical data**

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

8 Revision history

Table 59. Document revision history

Date	Revision	Changes
22-Sep-2008	1	Initial release.
30-Mar-2009	2	<p>"96-bit unique ID" feature added and I/O information clarified on page 1. Timers specified on page 1 (Motor control capability mentioned). Table 4: Timer feature comparison added. PB4, PB13, PB14, PB15, PB3/TRACESWO moved from Default column to Remap column, plus small additional changes in Table 5: Low-density STM32F103xx pin definitions. Figure 8: Memory map modified. References to V_{REF} removed: – Figure 1: STM32F103xx performance line block diagram modified, – Figure 11: Power supply scheme modified – Figure 34: ADC accuracy characteristics modified – Note modified in Table 49: ADC accuracy. Table 20: High-speed external user clock characteristics and Table 21: Low-speed external user clock characteristics modified. Note modified in Table 13: Maximum current consumption in Run mode, code with data processing running from Flash and Table 15: Maximum current consumption in Sleep mode, code running from Flash or RAM. Figure 17 shows a typical curve (title modified). ACC_{HSI} max values modified in Table 24: HSI oscillator characteristics. TFBGA64 package added (see Table 54 and Table 47). Small text changes.</p>
24-Sep-2009	3	<p>Note 5 updated and Note 4 added in Table 5: Low-density STM32F103xx pin definitions. V_{REFINT} and T_{Coeff} added to Table 12: Embedded internal reference voltage. Typical I_{DD_VBAT} value added in Table 16: Typical and maximum current consumptions in Stop and Standby modes. Figure 15: Typical current consumption on V_{BAT} with RTC on versus temperature at different V_{BAT} values added. f_{HSE_ext} min modified in Table 20: High-speed external user clock characteristics. C_{L1} and C_{L2} replaced by C in Table 22: HSE 4-16 MHz oscillator characteristics and Table 23: LSE oscillator characteristics ($f_{LSE} = 32.768$ kHz), notes modified and moved below the tables. Table 24: HSI oscillator characteristics modified. Conditions removed from Table 26: Low-power mode wakeup timings. Note 1 modified below Figure 21: Typical application with an 8 MHz crystal. Figure 28: Recommended NRST pin protection modified. Jitter added to Table 27: PLL characteristics on page 52. IEC 1000 standard updated to IEC 61000 and SAE J1752/3 updated to IEC 61967-2 in Section 5.3.10: EMC characteristics on page 53. C_{ADC} and R_{AIN} parameters modified in Table 46: ADC characteristics. R_{AIN} max values modified in Table 47: R_{AIN} max for $f_{ADC} = 14$ MHz. Small text changes.</p>